The following Listing of Claims will replace all prior versions, and listings, of claims in the application.

LISTING OF CLAIMS:

1.   (Cancelled).

2.   (Cancelled).

3.   (Cancelled).

4.   (Cancelled).

5.   (Cancelled).

6.   (Cancelled).

7.   (Cancelled).

8.   (Cancelled).

9.   (Cancelled).

10.   (Cancelled).

11.   (Cancelled).

12.   (Original)   Single-ended differential amplifier circuit comprising:

first unit having first and second active devices which have first, second, and third

terminals, respectively, wherein current flowing from the second terminal to the third

terminal has its quantity and direction being varying in dependant on the voltage driven to the

first terminal;

second unit having third and fourth devices which have first, second, and third

terminals, respectively, wherein current flowing from the second terminal to the third

terminal has its quantity and direction being varying in dependant on the voltage driven to the

first terminal; and

biasing means connected to the first terminals of the first and third active devices and

an input terminal, and connected to the second terminals of the second and fourth active

devices and an output terminal, for determining biasing points of the first and second units

such that the first and second units operates in a differential relationship with respect to a

signal driven to said input terminal, wherein said biasing means determines the biasing points

such that one of the first and second units is substantially active.

13.   (Original)   The single-ended differential amplifier circuit of Claim 12,

wherein said biasing means determines biasing points of the first and second units such that

current flowing from the first active device to the second active devices of the first unit is in

opposite phase to current flowing from the third active device to the fourth active device of

the second unit.

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14.   (Original)   The single-ended differential amplifier circuit of Claim 13,

wherein said first and second active devices are N type MOSFET and said third and fourth

active devices are P type MOSFET.